

R1LV3216R Series

32Mb Advanced LPSRAM (2M word x 16bit / 4M word x 8bit)

REJ03C0367-0100

Rev.1.00

2009.05.07

Description

The R1LV3216R Series is a family of low voltage 32-Mbit static RAMs organized as 2,097,152-word by 16-bit, fabricated by Renesas's high-performance 0.15um CMOS and TFT technologies.

The R1LV3216R Series is suitable for memory applications where a simple interfacing, battery operating and battery backup are the important design objectives.

The R1LV3216R Series is provided in 48-pin thin small outline package [TSOP (I): 12mm x 20mm with pin pitch of 0.5mm] and 52-pin micro thin small outline package [μ TSOP (II): 10.79mm x 10.49mm with pin pitch of 0.4mm]. It gives the best solution for compaction of mounting area as well as flexibility of wiring pattern of printed circuit boards.

Features

- Single 2.7~3.6V power supply
- Small stand-by current: 4 μ A (3.0V, typical)
- No clocks, No refresh
- All inputs and outputs are TTL compatible.
- Easy memory expansion by CS1#, CS2, LB# and UB#
- Common Data I/O
- Three-state outputs: OR-tie Capability
- OE# prevents data contention on the I/O bus

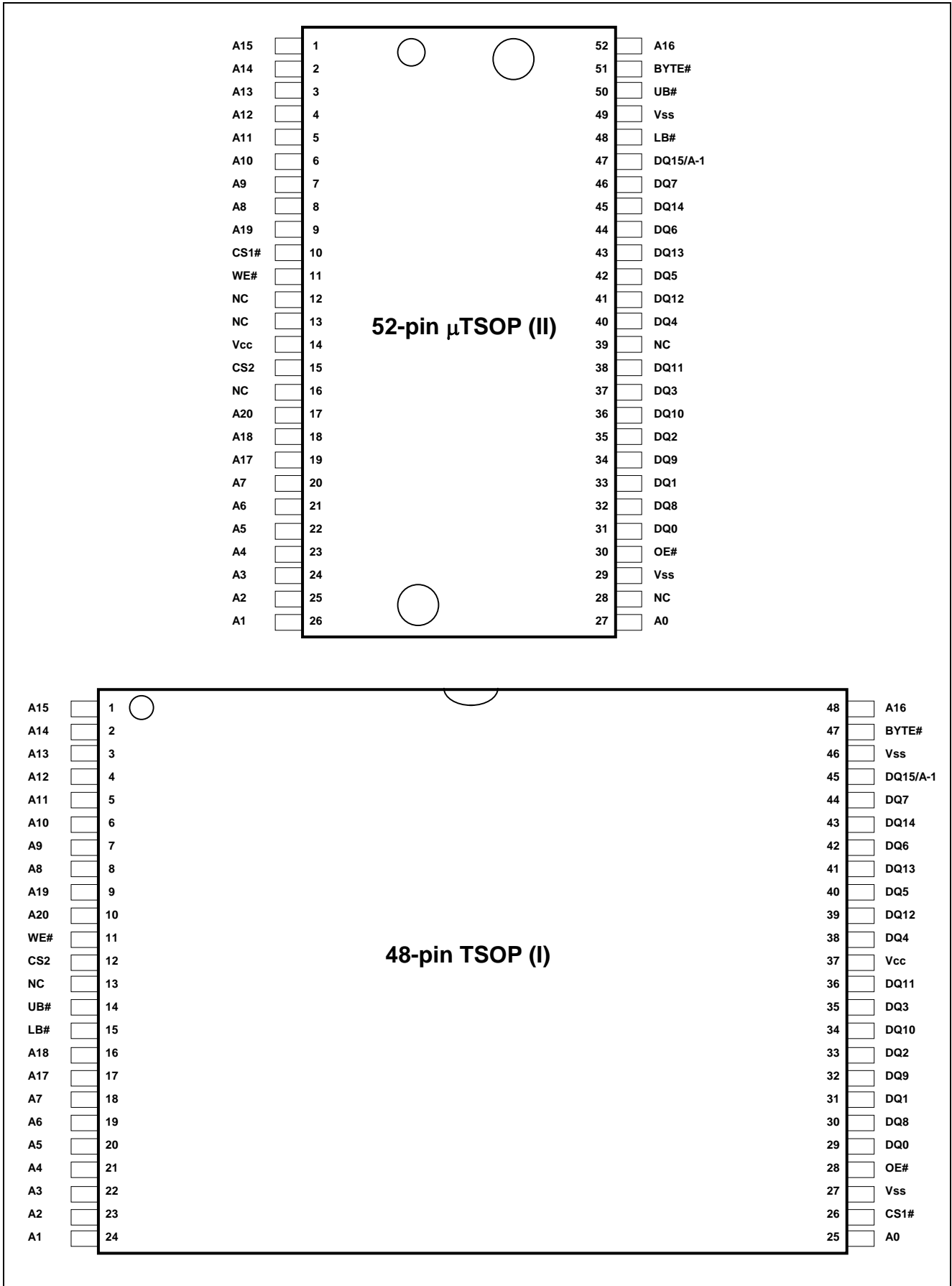
Ordering Information

Type No.	Access time	Package
R1LV3216RSA-5S%	55 ns	12mm x 20mm 48-pin plastic TSOP (I) (normal-bend type) (48P3R)
R1LV3216RSA-7S%	70 ns	
R1LV3216RSD-5S%	55 ns	350 mil 52-pin plastic μ -TSOP (II) (normal-bend type) (52PTG)
R1LV3216RSD-7S%	70 ns	

% - Temperature version; see table below

%	Temperature Range
R	0 ~ +70 °C
I	-40 ~ +85 °C

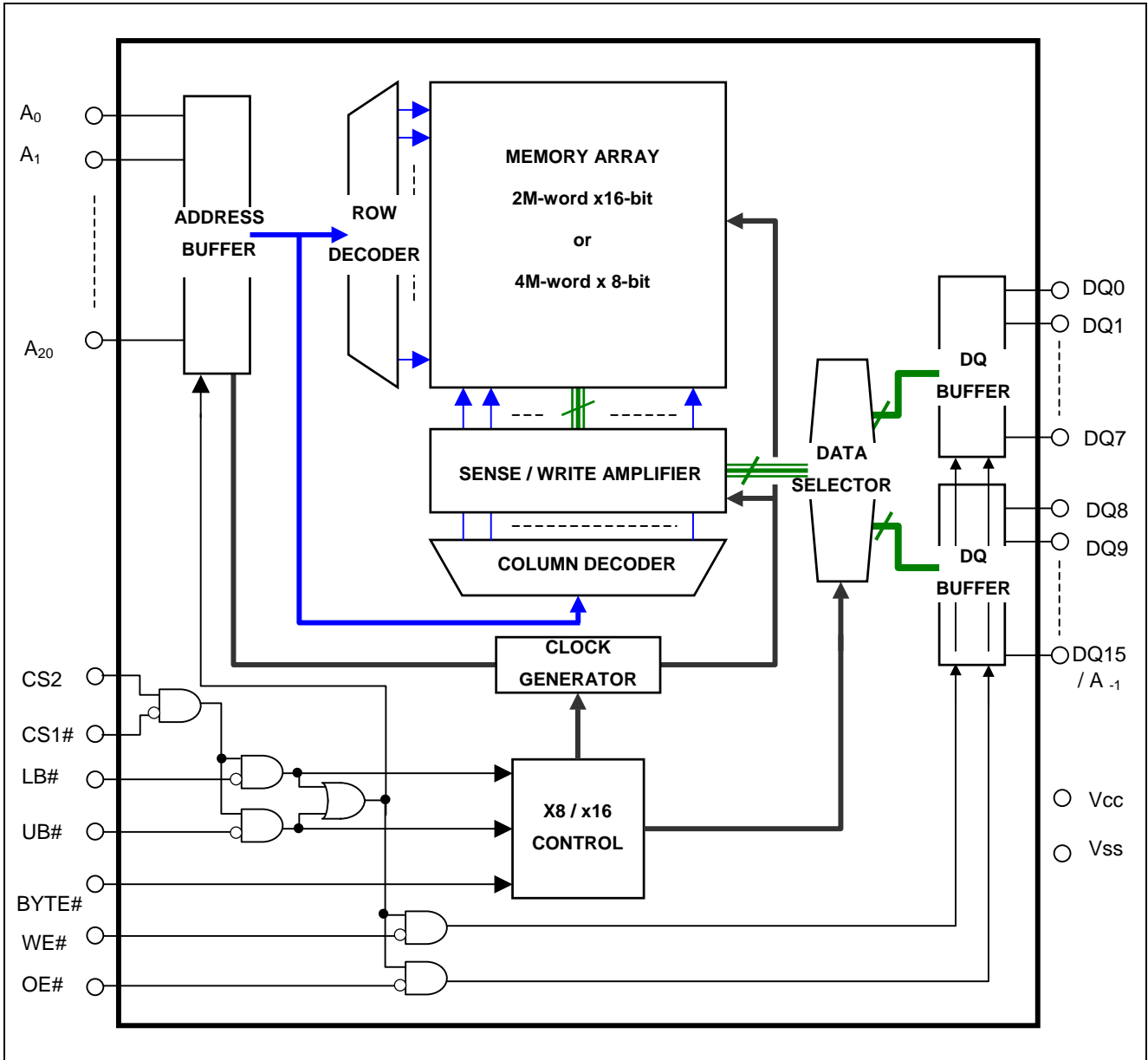
Pin Arrangement



Pin Description

Pin name	Function
Vcc	Power supply
Vss	Ground
A0 to A20	Address input (word mode)
A-1 to A20	Address input (byte mode)
DQ0 to DQ15	Data input/output
CS1#	Chip select 1
CS2	Chip select 2
WE#	Write enable
OE#	Output enable
LB#	Lower byte enable
UB#	Upper byte enable
BYTE#	Byte control mode enable
NC	Non connection

Block Diagram



Operation Table

CS1#	CS2	BYTE#	LB#	UB#	WE#	OE#	DQ0~7	DQ8~14	DQ15	Operation
H	X	X	X	X	X	X	High-Z	High-Z	High-Z	Stand-by
X	L	X	X	X	X	X	High-Z	High-Z	High-Z	Stand-by
X	X	H	H	H	X	X	High-Z	High-Z	High-Z	Stand-by
L	H	H	L	H	L	X	Din	High-Z	High-Z	Write in lower byte
L	H	H	L	H	H	L	Dout	High-Z	High-Z	Read in lower byte
L	H	H	L	H	H	H	High-Z	High-Z	High-Z	Output disable
L	H	H	H	L	L	X	High-Z	Din	Din	Write in upper byte
L	H	H	H	L	H	L	High-Z	Dout	Dout	Read in upper byte
L	H	H	H	L	H	H	High-Z	High-Z	High-Z	Output disable
L	H	H	L	L	L	X	Din	Din	Din	Word write
L	H	H	L	L	H	L	Dout	Dout	Dout	Word read
L	H	H	L	L	H	H	High-Z	High-Z	High-Z	Output disable
L	H	L	L	L	L	X	Din	High-Z	A-1	Byte write
L	H	L	L	L	H	L	Dout	High-Z	A-1	Byte read
L	H	L	L	L	H	H	High-Z	High-Z	A-1	Output disable

Note 1. H: V_{IH} L: V_{IL} X: V_{IH} or V_{IL}

2. When apply BYTE# = "L", please assign LB#=UB#="L".

Absolute Maximum Ratings

Parameter	Symbol	Value	unit
Power supply voltage relative to Vss	Vcc	-0.5 to +4.6	V
Terminal voltage on any pin relative to Vss	V_T	-0.5^{*1} to $V_{cc}+0.3^{*2}$	V
Power dissipation	P_T	0.7	W
Operation temperature	T_{opr}^{*3}	R ver.	0 to +70
		I ver.	-40 to +85
Storage temperature range	T_{stg}	-65 to 150	°C
Storage temperature range under bias	T_{bias}^{*3}	R ver.	0 to +70
		I ver.	-40 to +85

Note 1. -2.0V in case of AC (Pulse width ≤ 30 ns)

2. Maximum voltage is +4.6V.

3. Ambient temperature range depends on R/I-version. Please see table on page 1.

Recommended Operating Conditions

Parameter	Symbol	Min.	Typ.	Max.	Unit	Note	
Supply voltage	V _{CC}	2.7	3.0	3.6	V		
	V _{SS}	0	0	0	V		
Input high voltage	V _{IH}	2.4	-	V _{CC} +0.2	V		
Input low voltage	V _{IL}	-0.2	-	0.4	V	1	
Ambient temperature range	R ver.	T _a	0	-	+70	°C	2
	I ver.		-40	-	+85	°C	2

Note 1. -2.0V in case of AC (Pulse width ≤ 30ns)

2. Ambient temperature range depends on R/I-version. Please see table on page 1.

DC Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Input leakage current	I _{LI}	-	-	1	μA	V _{in} = V _{SS} to V _{CC}
Output leakage current	I _{LO}	-	-	1	μA	BYTE# ≥ V _{CC} -0.2V or BYTE# ≤ 0.2V CS1# =V _{IH} or CS2 =V _{IL} or OE# =V _{IH} or WE# =V _{IL} or LB# = UB# =V _{IH} , VI/O =V _{SS} to V _{CC}
Average operating current	I _{CC1}	-	40 ^{*1}	55	mA	Min. cycle, duty =100%, I/I/O = 0mA BYTE# ≥ V _{CC} -0.2V or BYTE# ≤ 0.2V CS1# =V _{IL} , CS2 =V _{IH} , Others = V _{IH} /V _{IL}
	I _{CC2}	-	3 ^{*1}	8	mA	Cycle =1μs, duty =100%, I/I/O = 0mA BYTE# ≥ V _{CC} -0.2V or BYTE# ≤ 0.2V CS1# ≤ 0.2V, CS2 ≥ V _{CC} -0.2V, V _{IH} ≥ V _{CC} -0.2V, V _{IL} ≤ 0.2V
Standby current	I _{SB}	-	0.1 ^{*1}	0.3	mA	BYTE# ≥ V _{CC} -0.2V or BYTE# ≤ 0.2V CS2 =V _{IL}
Standby current	I _{SB1}	-	4 ^{*1}	12	μA	~+25°C V _{in} ≥ 0V BYTE# ≥ V _{CC} -0.2V or BYTE# ≤ 0.2V
		-	7 ^{*2}	24	μA	~+40°C (1) 0V ≤ CS2 ≤ 0.2V or (2) CS1# ≥ V _{CC} -0.2V, CS2 ≥ V _{CC} -0.2V or
		-	-	50	μA	~+70°C (3) LB# = UB# ≥ V _{CC} -0.2V, CS1# ≤ 0.2V, CS2 ≥ V _{CC} -0.2V
		-	-	80	μA	~+85°C
Output high voltage	V _{OH}	2.4	-	-	V	BYTE# ≥ V _{CC} -0.2V or BYTE# ≤ 0.2V I _{OH} = -0.5mA
Output low voltage	V _{OL}	-	-	0.4	V	BYTE# ≥ V _{CC} -0.2V or BYTE# ≤ 0.2V I _{OL} = 2mA

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (T_a = 25°C), and not 100% tested.

2. Typical parameter indicates the value for the center of distribution at 3.0V (T_a = 40°C), and not 100% tested.

Capacitance

(Ta =25°C, f =1MHz)

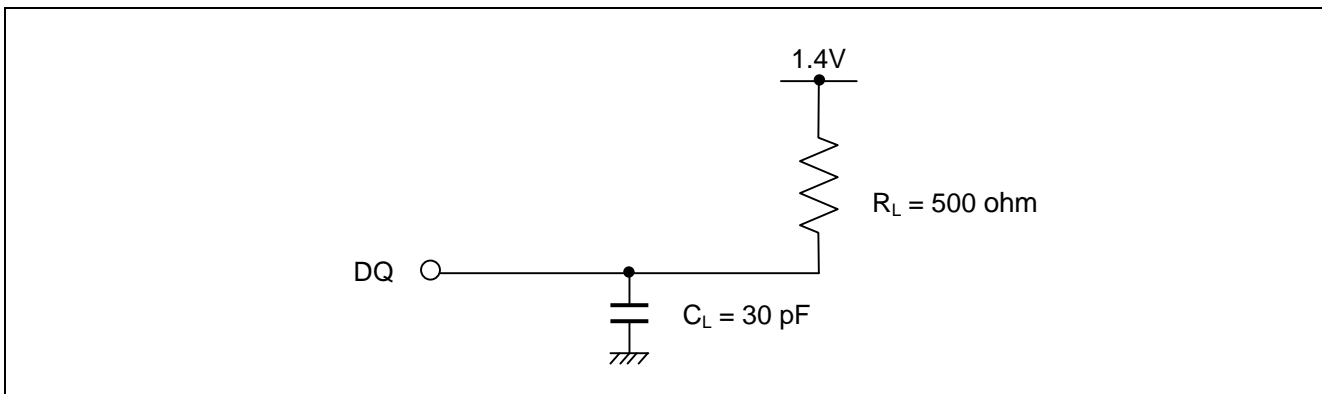
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions	Note
Input capacitance	C _{in}	-	-	10	pF	V _{in} =0V	1
Input / output capacitance	C _{I/O}	-	-	10	pF	V _{I/O} =0V	1

Note1. This parameter is sampled and not 100% tested.

AC Characteristics

Test Conditions (V_{cc} = 2.7V ~ 3.6V, Ta = 0 ~ +70°C / -40 ~ +85°C^{*1})

- Input pulse levels: V_{IL} = 0.4V, V_{IH} = 2.4V
- Input rise and fall time: 5ns
- Input and output timing reference level: 1.4V
- Output load: See figures (Including scope and jig)



Note1. Ambient temperature range depends on R/I-version. Please see table on page 1.

Read Cycle

Parameter	Symbol	R1LV3216R**-5S		R1LV3216R**-7S		Unit	Note
		Min.	Max.	Min.	Max.		
Read cycle time	t _{RC}	55	-	70	-	ns	
Address access time	t _{AA}	-	55	-	70	ns	
Chip select access time	t _{ACS1}	-	55	-	70	ns	
	t _{ACS2}	-	55	-	70	ns	
Output enable to output valid	t _{OE}	-	25	-	35	ns	
Output hold from address change	t _{OH}	10	-	10	-	ns	
LB#, UB# access time	t _{BA}	-	55	-	70	ns	
Chip select to output in low-Z	t _{CLZ1}	10	-	10	-	ns	2,3
	t _{CLZ2}	10	-	10	-	ns	2,3
LB#, UB# enable to low-Z	t _{BLZ}	5	-	5	-	ns	2,3
Output enable to output in low-Z	t _{OLZ}	5	-	5	-	ns	2,3
Chip deselect to output in high-Z	t _{CHZ1}	0	20	0	25	ns	1,2,3
	t _{CHZ2}	0	20	0	25	ns	1,2,3
LB#, UB# disable to high-Z	t _{BHZ}	0	20	0	25	ns	1,2,3
Output disable to output in high-Z	t _{OHZ}	0	20	0	25	ns	1,2,3

Write Cycle

Parameter	Symbol	R1LV3216R**-5S		R1LV3216R**-7S		Unit	Note
		Min.	Max.	Min.	Max.		
Write cycle time	t_{WC}	55	-	70	-	ns	
Address valid to end of write	t_{AW}	50	-	65	-	ns	
Chip select to end of write	t_{CW}	50	-	65	-	ns	5
Write pulse width	t_{WP}	40	-	55	-	ns	4
LB#, UB# valid to end of write	t_{BW}	50	-	65	-	ns	
Address setup time	t_{AS}	0	-	0	-	ns	6
Write recovery time	t_{WR}	0	-	0	-	ns	7
Data to write time overlap	t_{DW}	25	-	35	-	ns	
Data hold from write time	t_{DH}	0	-	0	-	ns	
Output enable from end of write	t_{OW}	5	-	5	-	ns	2
Output disable to output in high-Z	t_{OHZ}	0	20	0	25	ns	1,2
Write to output in high-Z	t_{WHZ}	0	20	0	25	ns	1,2

Note1. t_{CHZ} , t_{OHZ} , t_{WHZ} and t_{BHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referred to output voltage levels.

2. This parameter is sampled and not 100% tested.

3. At any given temperature and voltage condition, t_{HZ} max is less than t_{LZ} min both for a given device and from device to device.

4. A write occurs during the overlap of a low CS1#, a high CS2, a low WE# and a low LB# or a low UB#. A write begins at the latest transition among CS1# going low, CS2 going high, WE# going low and LB# going low or UB# going low .

A write ends at the earliest transition among CS1# going high, CS2 going low, WE# going high and LB# going high or UB# going high. t_{WP} is measured from the beginning of write to the end of write.

5. t_{CW} is measured from the later of CS1# going low or CS2 going high to end of write.

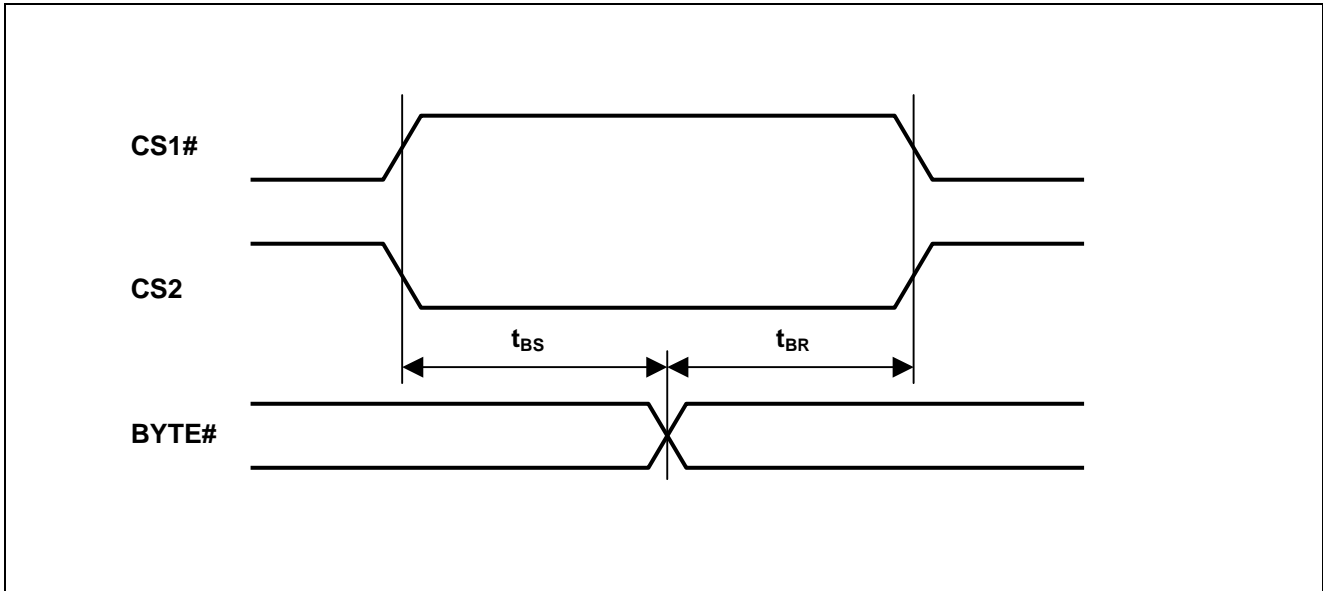
6. t_{AS} is measured the address valid to the beginning of write.

7. t_{WR} is measured from the earliest of CS1# or WE# going high or CS2 going low to the end of write cycle.

BYTE# Timing Conditions

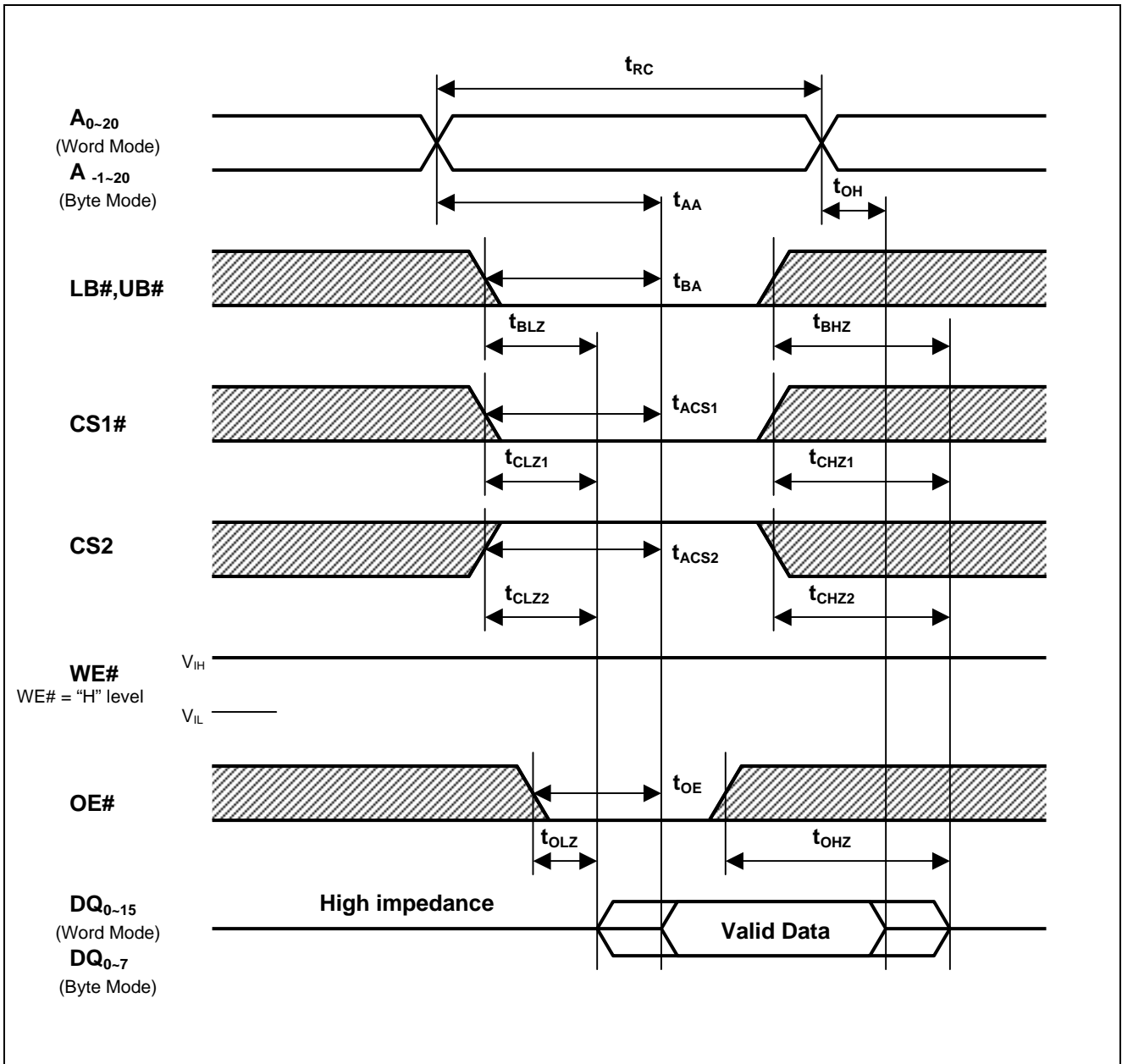
Parameter	Symbol	R1LV3216R**-5S		R1LV3216R**-7S		Unit	Note
		Min.	Max.	Min.	Max.		
Byte setup time	t_{BS}	5	-	5	-	ms	
Byte recovery time	t_{BR}	5	-	5	-	ms	

BYTE# Timing Waveforms



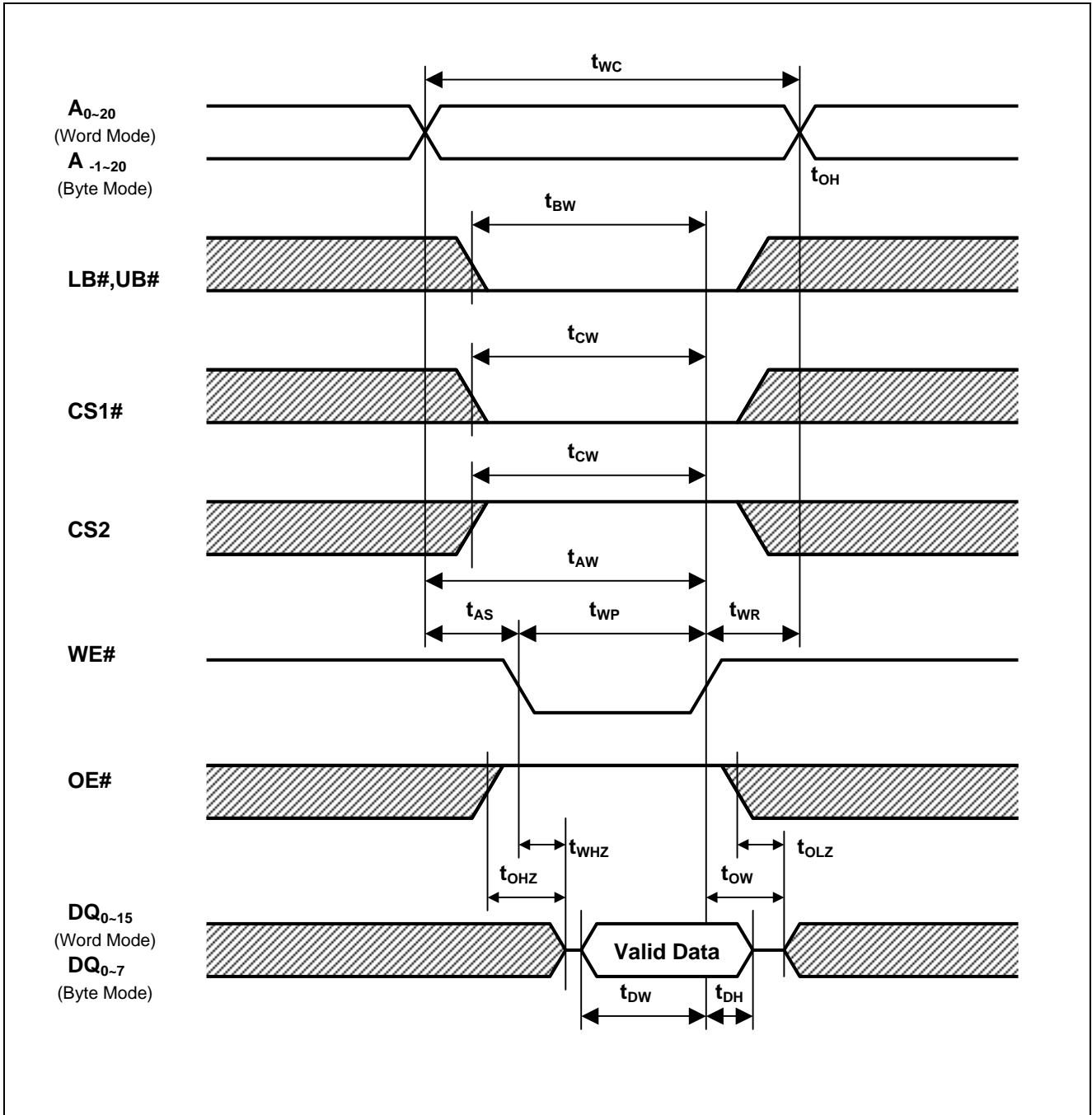
Timing Waveforms

Read Cycle^{*1}



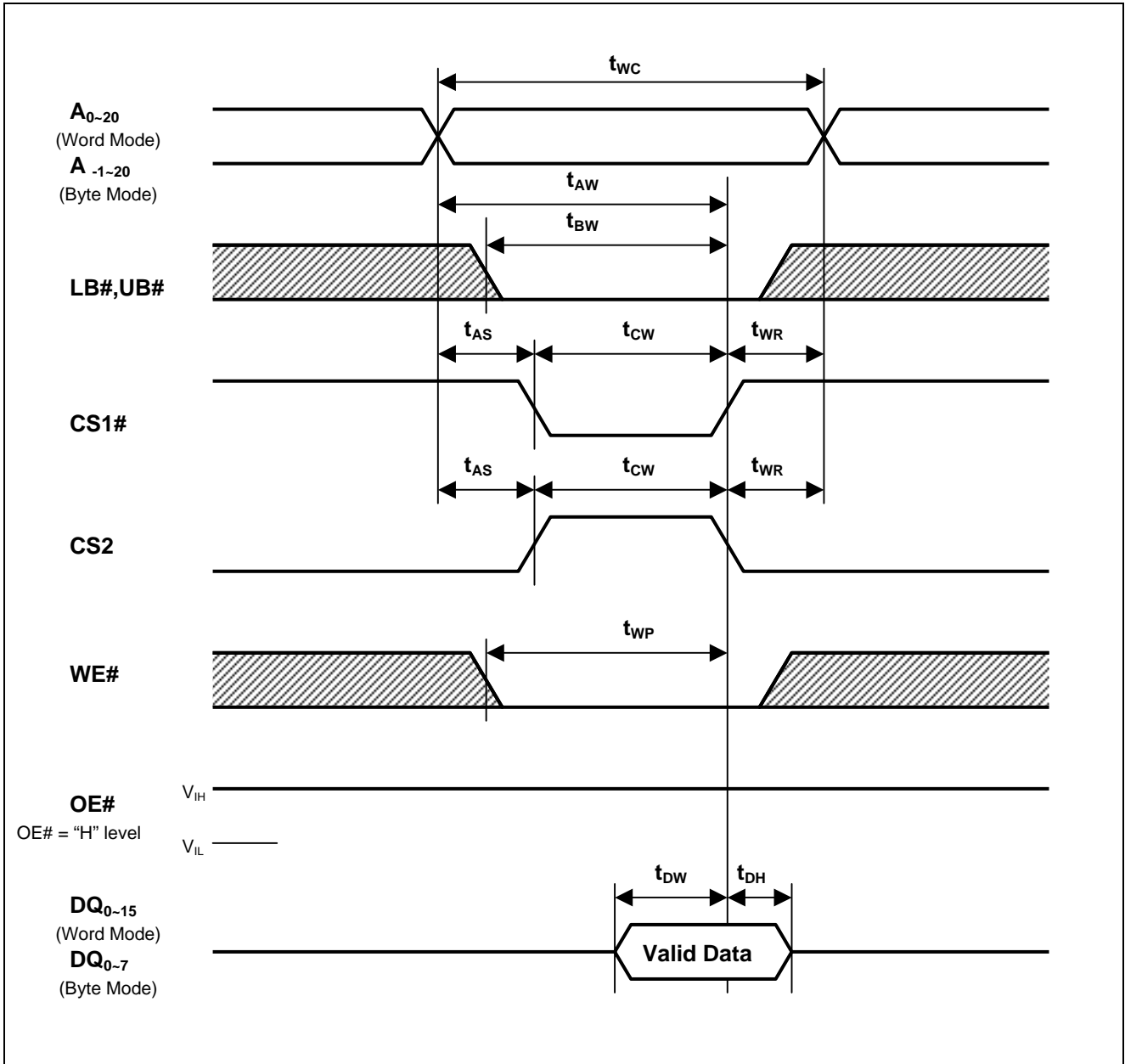
Note1. $BYTE\# \geq V_{CC} - 0.2V$ or $BYTE\# \leq 0.2V$

Write Cycle (1)^{*1} (WE# CLOCK)



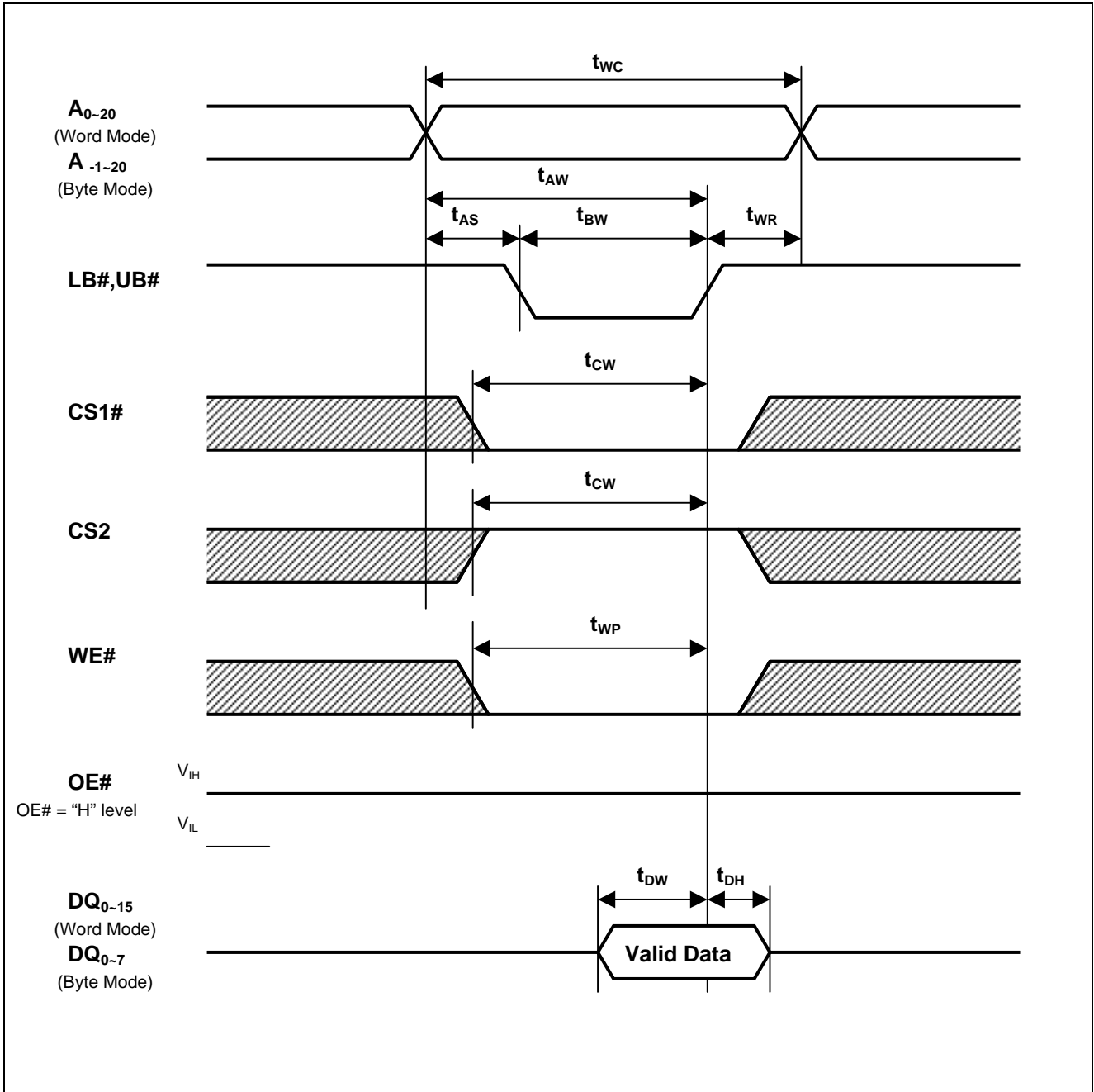
Note1. $BYTE\# \geq V_{CC} - 0.2V$ or $BYTE\# \leq 0.2V$

Write Cycle (2)^{*1} (CS1#, CS2 CLOCK)



Note1. BYTE# $\geq V_{CC} - 0.2V$ or BYTE# $\leq 0.2V$

Write Cycle (3)^{*1} (LB#, UB# CLOCK)



Note1. BYTE# ≥ V_{CC} - 0.2V or BYTE# ≤ 0.2V

Low Vcc Data Retention Characteristics

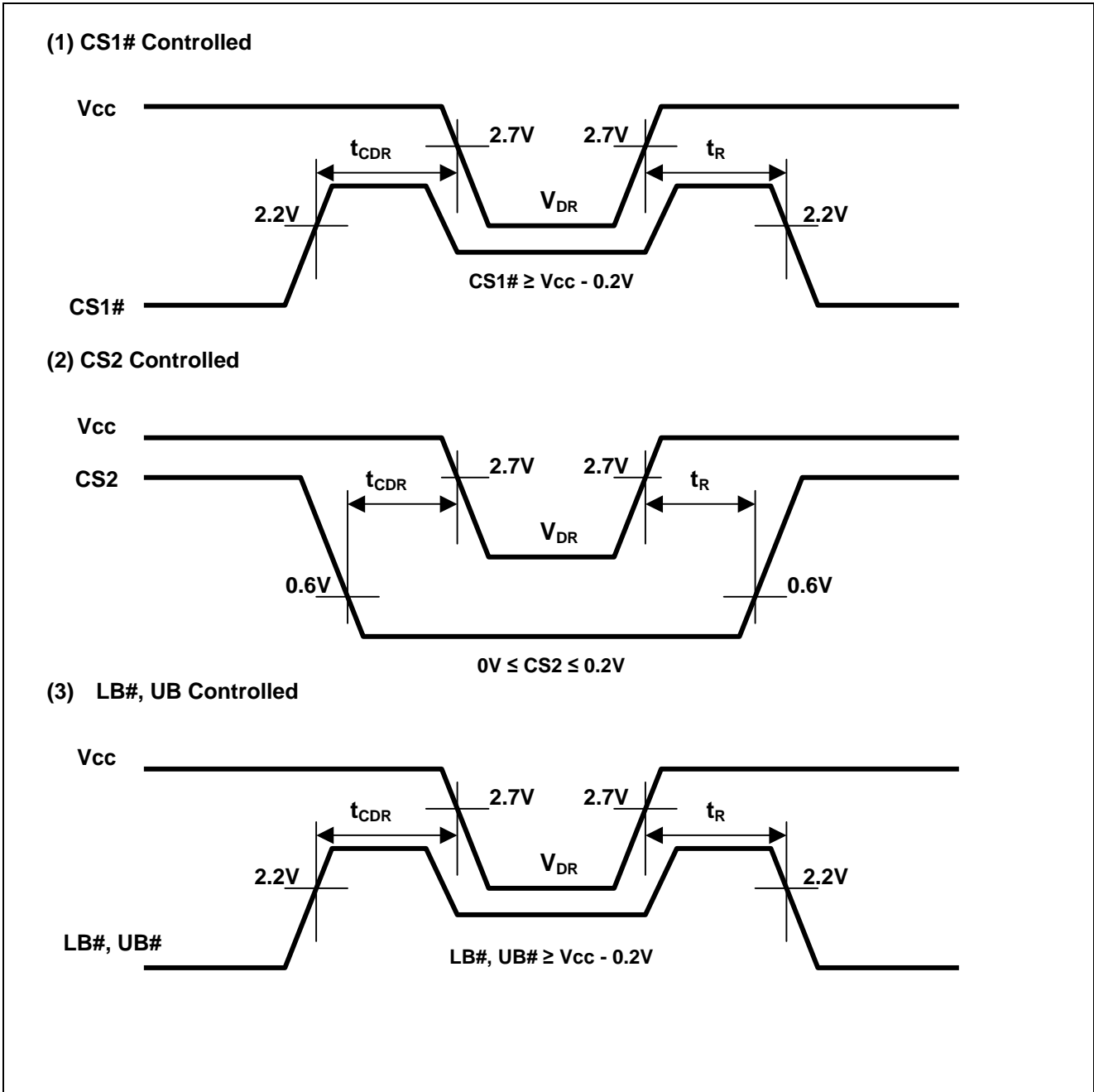
Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions ³	
V _{CC} for data retention	V _{DR}	2.0	-	3.6	V	V _{in} ≥ 0V BYTE# ≥ V _{CC} - 0.2V or BYTE# ≤ 0.2V (1) 0V ≤ CS2 ≤ 0.2V or (2) CS1# ≥ V _{CC} - 0.2V, CS2 ≥ V _{CC} - 0.2V or (3) LB# = UB# ≥ V _{CC} - 0.2V, CS1# ≤ 0.2V, CS2 ≥ V _{CC} - 0.2V	
Data retention current	I _{CCDR}	-	4 ^{*1}	12	μA	~+25°C	V _{in} ≥ 0V BYTE# ≥ V _{CC} - 0.2V or BYTE# ≤ 0.2V (1) 0V ≤ CS2 ≤ 0.2V or (2) CS1# ≥ V _{CC} - 0.2V, CS2 ≥ V _{CC} - 0.2V or (3) LB# = UB# ≥ V _{CC} - 0.2V, CS1# ≤ 0.2V, CS2 ≥ V _{CC} - 0.2V
		-	7 ^{*2}	24	μA	~+40°C	
		-	-	50	μA	~+70°C	
		-	-	80	μA	~+85°C	
Chip select to data retention time	t _{CDR}	0	-	-	ns	See retention waveform.	
Operation recovery time	t _R	5	-	-	ms		

Note 1. Typical parameter indicates the value for the center of distribution at 3.0V (T_a = 25°C), and not 100% tested.

2. Typical parameter indicates the value for the center of distribution at 3.0V (T_a = 40°C), and not 100% tested.

3. CS2 also controls address buffer, WE# buffer, CS1# buffer, OE# buffer, LB#, UB# buffer and Din buffer. If CS2 controls data retention mode, V_{in} levels (address, WE#, OE#, CS1#, LB#, UB#, I/O) can be in the high impedance state. If CS1# controls data retention mode, CS2 must be CS2 ≥ V_{CC} - 0.2V or 0V ≤ CS2 ≤ 0.2V. The other input levels (address, WE#, OE#, CS1#, LB#, UB#, I/O) can be in the high impedance state.

Low Vcc Data Retention Timing Waveforms*1



Note1. BYTE# $\geq V_{CC} - 0.2V$ or BYTE# $\leq 0.2V$

Revision History

R1LV3216R Series Data Sheet

Rev.	Date	Contents of Revision	
		Page	Description
0.01	Mar.24, 2008	-	Initial issue: Preliminary Data Sheet
1.00	May 07, 2009	-	Finalized
		5	Operation Table corrected
		6	Error corrected: I_{SB} Test condition $CS2=V_{IH} \rightarrow V_{IL}$

Notes:

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